

**IRF240R, IRF241R
IRF242R, IRF243R**

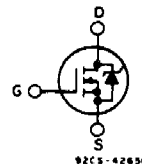
Avalanche Energy Rated N-Channel Power MOSFETs

16A and 18A, 200V, 150V
 $r_{DS(on)} = 0.18\Omega$ and 0.22Ω

Features:

- Single pulse avalanche energy rated
- SOA is power-dissipation limited
- Nanosecond switching speeds
- Linear transfer characteristics
- High input impedance

TERMINAL DIAGRAM

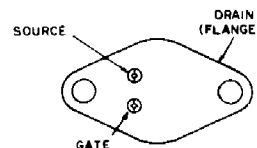


N-CHANNEL ENHANCEMENT MODE

The IRF240R, IRF241R, IRF242R and IRF243R are advanced power MOSFETs designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. These are n-channel enhancement-mode silicon-gate power field-effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high-power bipolar switching transistors requiring high speed and low gate-drive power. These types can be operated directly from integrated circuits.

The IRF-types are supplied in the JEDEC TO-204AE steel package.

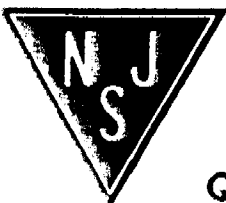
TERMINAL DESIGNATION



JEDEC TO-204AE

Absolute Maximum Ratings

Parameter	IRF240R	IRF241R	IRF242R	IRF243R	Units
V_{DS} Drain - Source Voltage ①	200	150	200	150	V
V_{DGR} Drain - Gate Voltage ($R_{GS} = 20\text{ K}\Omega$) ①	200	150	200	150	V
I_D @ $T_C = 25^\circ\text{C}$ Continuous Drain Current	18	18	16	16	A
I_D @ $T_C = 100^\circ\text{C}$ Continuous Drain Current	11	11	10	10	A
I_{DM} Pulsed Drain Current ③	72	72	64	64	A
V_{GS} Gate - Source Voltage	± 20				V
P_D @ $T_C = 25^\circ\text{C}$ Max. Power Dissipation	125 (See Fig. 14)				W
Linear Derating Factor	1.0 (See Fig. 14)				W/ $^\circ\text{C}$
E_{AS} Single Pulse Avalanche Energy Rating ④	580				mJ
T_J Operating Junction and T_{slg} Storage Temperature Range	-55 to 150				$^\circ\text{C}$
Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				$^\circ\text{C}$



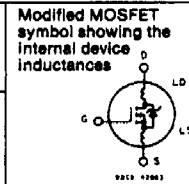
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Quality Semi-Conductors

**IRF240R, IRF241R
IRF242R, IRF243R**

Electrical Characteristics @ $T_c = 25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
BV _{DSS} Drain - Source Breakdown Voltage	IRF240R IRF242R	200	—	—	V	V _{GS} = 0V
	IRF241R IRF243R	150	—	—	V	I _D = 250 μ A
V _{GS(th)} Gate Threshold Voltage	ALL	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250 μ A
I _{GSS} Gate-Source Leakage Forward	ALL	—	—	100	nA	V _{GS} = 20V
I _{GSS} Gate-Source Leakage Reverse	ALL	—	—	-100	nA	V _{GS} = -20V
I _{DSS} Zero Gate Voltage Drain Current	ALL	—	—	250	μ A	V _{DS} = Max. Rating, V _{GS} = 0V
		—	—	1000	μ A	V _{DS} = Max. Rating x 0.8, V _{GS} = 0V, T _c = 125°C
I _{D(on)} On-State Drain Current ②	IRF240R IRF241R	18	—	—	A	V _{DS} > I _{D(on)} x R _{DSON} max., V _{GS} = 10V
	IRF242R IRF243R	18	—	—	A	
	ALL	—	—	—	—	
R _{DSON} Static Drain-Source On-State Resistance ②	IRF240R IRF241R	—	0.14	0.18	Ω	V _{GS} = 10V, I _D = 10A
	IRF242R IRF243R	—	0.20	0.22	Ω	
	ALL	—	—	—	—	
g _{fs} Forward Transconductance ③	ALL	8.0	9.0	—	S(Ω)	V _{DS} > I _{D(on)} x R _{DSON} max., I _D = 10A
C _{iss} Input Capacitance	ALL	—	1275	—	pF	V _{GS} = 0V, V _{DS} = 25V, f = 1.0 MHz
C _{oss} Output Capacitance	ALL	—	500	—	pF	See Fig. 10
C _{rss} Reverse Transfer Capacitance	ALL	—	180	—	pF	
t _{D(on)} Turn-On Delay Time	ALL	—	16	30	ns	V _{DD} = 75V, I _D = 10A, Z ₀ = 4.7 Ω
t _r Rise Time	ALL	—	27	60	ns	See Fig. 17
t _{D(off)} Turn-Off Delay Time	ALL	—	40	80	ns	(MOSFET switching times are essentially independent of operating temperature.)
t _f Fall Time	ALL	—	31	60	ns	
Q _g Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	—	43	60	nC	V _{GS} = 10V, I _D = 22A, V _{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q _{gs} Gate-Source Charge	ALL	—	16	—	nC	
Q _{gd} Gate-Drain ("Miller") Charge	ALL	—	27	—	nC	
L _D Internal Drain Inductance	ALL	—	5.0	—	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die.
L _S Internal Source Inductance	ALL	—	12.5	—	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.



Thermal Resistance

R _{thJC} Junction-to-Case	ALL	—	—	1.0	°C/W	
R _{thCS} Case-to-Sink	ALL	—	0.1	—	°C/W	Mounting surface flat, smooth, and greased.
R _{thJA} Junction-to-Ambient	ALL	—	—	30	°C/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I _S Continuous Source Current (Body Diode)	IRF240R IRF241R	—	—	18	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier.
	IRF242R IRF243R	—	—	18	A	
	ALL	—	—	—	—	
I _{SM} Pulse Source Current (Body Diode) ③	IRF240R IRF241R	—	—	72	A	
	IRF242R IRF243R	—	—	64	A	
	ALL	—	—	—	—	
V _{SD} Diode Forward Voltage ②	IRF240R IRF241R	—	—	2.0	V	T _c = 25°C, I _S = 18A, V _{GS} = 0V
	IRF242R IRF243R	—	—	1.9	V	T _c = 25°C, I _S = 16A, V _{GS} = 0V
	ALL	—	—	—	—	
t _r Reverse Recovery Time	ALL	—	650	—	ns	T _J = 150°C, I _F = 18A, dI _F /dt = 100A/ μ s
Q _{rr} Reverse Recovered Charge	ALL	—	4.1	—	μ C	T _J = 150°C, I _F = 18A, dI _F /dt = 100A/ μ s
t _{on} Forward Turn-on Time	ALL	—	—	—	—	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .

① T_J = 25°C to 150°C. ② Pulse Test: Pulse width $\leq 300\mu$ s, Duty Cycle $\leq 2\%$.

③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

④ V_{DD} = 50V, starting T_J = 25°C, L = 2.7 mH, R_{DS(on)} = 50 Ω , I_{peak} = 18A. See figures 15, 16.